NSN 5961-01-267-9739

Photo Semiconductor Device - Page 1 of 1

View Online at https://aerobasegroup.com/nsn/5961-01-267-9739

Inclosure Material:

Glass

Overall Length:

0.115 inches

Overall Diameter:

0.062 inches

Function For Which Designed:

Phototransistor

Internal Configuration:

Junction contact

Mounting Method:

Press fit

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

50.0 collector to emitter voltage, dc and 7.0 emitter to collector voltage, dc

Current Rating Per Characteristic:

50.00 milliamperes forward current, total rms nanoamperes

Power Rating Per Characteristic:

50.0 milliwatts small-signal input power, common-collector preset

Maximum Operating Tempurature Per Measurement Point:

125.0 degrees celsius ambient air

Special Features:

Plate phototransistor mtg and one ft buss wire 20 awg; internal junction configuration: npn

Terminal Type And Quantity:

3 uninsulated wire lead

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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